

**A SEMICONDUCTOR DEVICE HAVING MULTIPLE WORK FUNCTIONS
AND METHOD OF MANUFACTURE THEREFOR**

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device, a method of manufacture therefor, and a method for manufacturing an integrated circuit. The semiconductor device (100), among other possible elements, includes a first transistor (120) located over a semiconductor substrate (110), wherein the first transistor (120) has a metal gate electrode (135) having a work function, and a second transistor (160) located over the semiconductor substrate (110) and proximate the first transistor (120), wherein the second transistor (160) has a plasma altered metal gate electrode (175) having a different work function.